



Features:

- Frequency Range: 6 22 GHz
- P1dB: 18.5 dBm @Vdd=5V
- P3dB: 19.5 dBm @Vdd=5V
- Gain: 14 dB
- Vdd =3 to 6 V
- Ids = 130 mA
- Input and Output Fully Matched to 50 Ω

Applications:

- Communication systems
- Microwave instrumentations
- ECM

Description:



The MMA-062020 is a broadband GaAs MMIC general purpose gain block for 19.5dBm saturated maximum output power and high gain over full 6 to 22GHz frequency range. This amplifier was optimally designed for broadband applications requiring flat gain with excellent input and output port matches.

Absolute Maximum Ratings: (Ta= 25 °C)*

	DADAMETERO		Min.	Maria		
SYMBOL	PARAMETERS	UNITS		Max.		
Vd1, Vd2	Drain-Supply Voltage	V		6.5		
ld1	Drain Supply Current	mA		70		
ld2	Drain Supply Current	mA		84		
Pin max	RF Input Power	dBm		20		
Toper	Operating Temperature	°C		-40 to +85		
Tch	Channel Temperature	°C		+150		
Tstg	Storage Temperature	°C		-55 to +165		
Tmax	Max. Assembly Temp (60 sec max)	°C		+300		
*Operation of this device above any one of these parameters may cause permanent damage.						





Electrical Specifications: Vds=5V, Ids=130mA, Ta=25 °C Z0=50 ohm					
Parameter	Units	Typical Data			
Frequency Range	GHz	6 - 22			
Gain (Typ / Min)	dB	14 / 13.5			
Gain Flatness (Typ / Max)	+/-dB	0.8 / 1			
Input RL(Typ/Max)	dB	8/6			
Output RL(Typ/Max)	dB	10/7			
Output P1dB(Typ/Min)	dBm	18.5/18			
Output IP3 (1)	dBm	28			
Output Psat(Typ/Min)	dBm	19.5/18.5			
Operating Current at P1dB (Typ/Max)	mA	130 / 132			
Thermal Resistance	°C /W	65			
(1) Output IP3 is measured with two tones at output	ut power of 0 dBm/tone separate	d by 20 MHz.			







P-1 and Psat vs. Frequency

Pout[dBm], Gain[dB], and Ids[mA] vs. Input power [dBm]







Bias dependent P1 vs. Frequency



Bias dependent P-3 vs. Frequency



S21(dB) over voltage



S11(dB) over Voltage



S22(dB) over Voltage

Typical Bias dependent RF Performance:





Typical Over Temperature RF Performance: Vds=5V, Ids=130mA, Z0=50 ohm, Ta=25 °C







Applications

The **MMA-062020-C3** is a GaAS PHEMT amplifier designed for Class-A condition, flat gain performance from 6GHz to 22GHz. It is applicable for cascadable gain stage for EW amplifiers, buffer stages, LO drivers, and transmitter amplifiers used in commercial communication systems. This amplifier is provided as a 3x3mm QFN package, and the packaged amplifier is fully compatible with industry standard high volume surface mount PCB assembly processes.

Biasing and Operation

The **MMA-062020-C3** is normally biased with a single positive supply voltage connected to both Vd1 and Vd2 pins. The recommended drain supply voltages are 3 to 6 volts. RF input and output ports are DC decoupled internally. Typical DC supply connection with bi-passing capacitors for the **MMA-062020-C3** is shown in following pages.

Assembly Techniques

GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly. MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability.





Package Pin-out:



Pin	Description	
2	RF Input	
8	RF Output	
12	Vd1	
10	Vd2	
1, 3, 7, 9, 13 (center pad)	Ground	
4, 5, 6, 11	N/C	











Recommended Application Board Design:

Board Material is 10mil (Dielectric) thickness Rogers 4350B with 0.5oz cupper clads. Board is soldered on a gold plated solid cupper block and adequate heat-sinking is required for 0.7W total maximum power dissipation.





Recommended Application Board Design:

Board Material is 10mil (Dielectric) thickness Rogers 4350B with 0.5oz cupper clads. The board material and mounting pattern, as defined in the data sheet, optimizes RF performance and is strongly recommended. An electronic drawing of the land pattern is available upon request from *MwT* Sales & Application Engineering.

